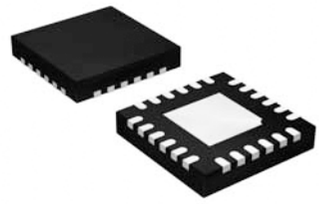
chanhvinh.com

STSPIN840

Compact dual brushed DC motor driver

Datasheet - production data



QFN 4 x 4 - 24 lead

Features

- Operating voltage from 7 to 45 V
- Maximum output current 1.5 A_{rms}
- R_{DSon} HS + LS = 1 Ω typ.
- Current control with adjustable OFF time
- Current sensing based on external shunt resistors
- Full protections set
  - Non-dissipative overcurrent protection
  - Short-circuit protection
  - Undervoltage lockout
  - Thermal shutdown
- Parallel operation mode achieving single full-bridge configuration with output I_{RMS} = 3 A_{rms} and R_{DSon} HS + LS = 500 mΩ typ.
- Low standby current consumption

Applications

- Industrial automation and service robots
- Medical and health care
- ATM and money handling machines
- Stage lighting
- Thermal printers
- Textile and sewing machines
- Vending machines
- Office and home automation

Description

The STSPIN840 is a compact brushed DC motor driver able to drive two bi-directional brushed DC motors simultaneously. It integrates, in a very small 4 x 4 mm QFN package, both the control logic and a fully protected low R_{DSon} dual full-bridge power stage.

Thanks to a dedicated PARALLEL input pin the parallel mode function can be enabled, transforming the device in an equivalent and more powerful single full-bridge able to deliver up to 3A_{rms} current at an equivalent HS + LS R_{DSon} of 500 mΩ.

The STSPIN840 embeds two independent PWM current controllers (one for each full bridge) based on user settable values of reference voltage and OFF time.

The devices can be forced in a low consumption state reducing the total current consumption down to less than 45 µA.

As with all other devices from the STSPIN family, the STSPIN840 integrates a complete set of protections for the power stages (non-dissipative overcurrent, thermal shutdown, short-circuit and undervoltage lockout) making it a bulletproof solution for the new wave of demanding industrial applications.

This is information on a product in full production. www.st.com

chanhvinh.com

Contents

1 **Block diagram** 5

2 **Electrical data** 6

2.1 Absolute maximum ratings 6

2.2 Recommended operating conditions 6

2.3 Thermal data 7

2.4 ESD protection ratings 7

3 **Electrical characteristics** 8

4 **Pin connection** 10

5 **Detailed description** 12

5.1 Power supply and standby 12

5.2 Logic inputs 13

PARALLEL mode 14

5.3 PWM current control 15

TOFF adjustment 17

5.4 Device protections 18

5.4.1 Overcurrent and short-circuit protections 18

5.4.2 Thermal shutdown 20

5.4.3 Blanking time 21

5.5 ESD protection strategy 22

6 **Typical applications** 23

7 **Layout recommendations** 24

8 **Package information** 25

8.1 TFQFPN TFQFPN 4 x 4 x 1.05 - 24 L package information 25

9 **Ordering information** 27

10 **Revision history** 27

chanhvinh.com

List of tables

Table 1. Absolute maximum ratings . . . 6
Table 2. Recommended operating conditions . . . 6
Table 3. Thermal data . . . 7
Table 4. ESD protection ratings . . . 7
Table 5. Electrical characteristics . . . 8
Table 6. Pin description . . . 10
Table 7. Truth table . . . 13
Table 8. ON and slow decay states . . . 15
Table 9. Typical application values . . . 23
Table 10. TFQFPN 4 x 4 x 1.05 - 24 L package mechanical data . . . 26
Table 11. Device summary . . . 27
Table 12. Document revision history . . . 27

chanhvinh.com

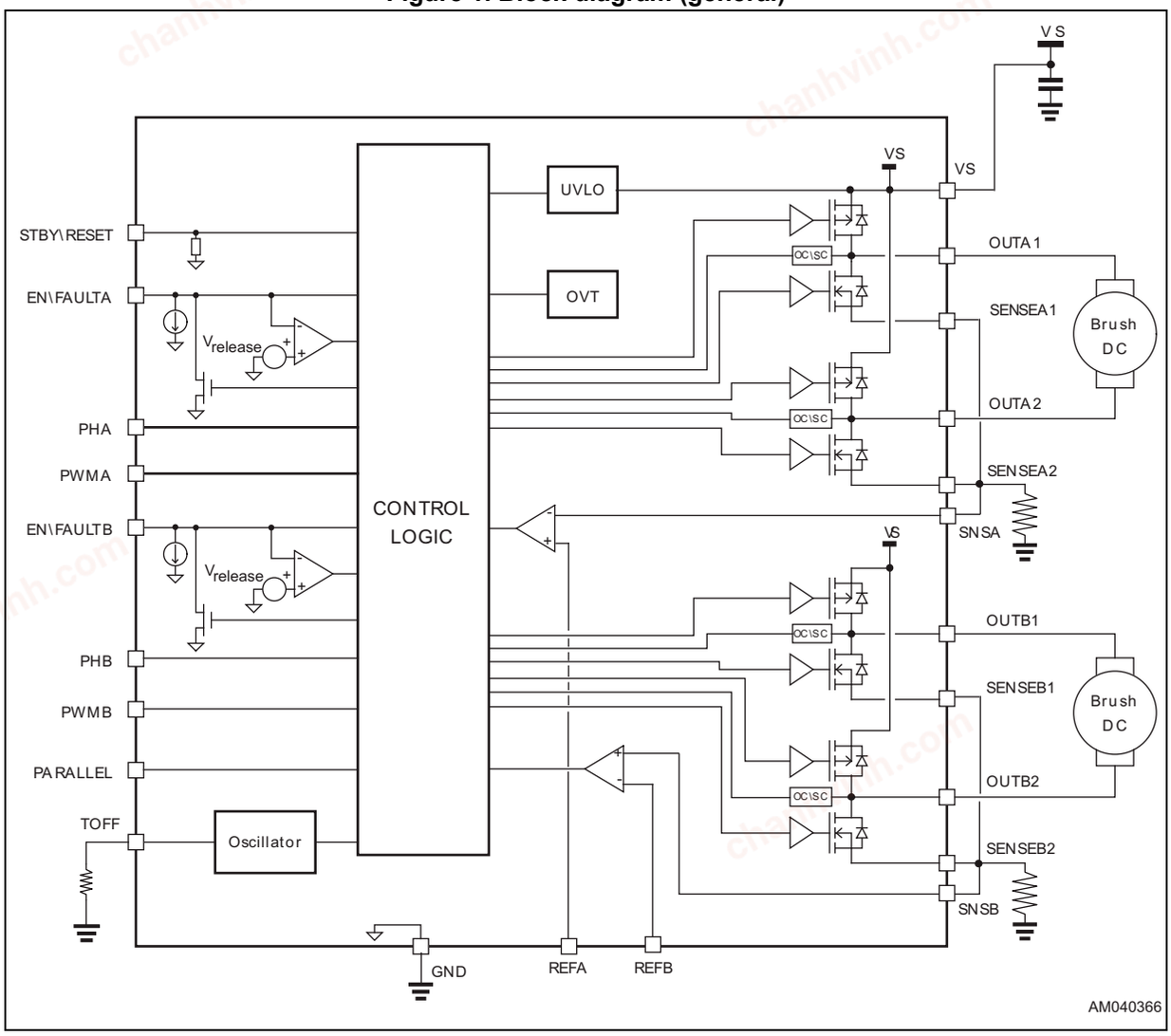
List of figures

Figure 1. Block diagram (general) . . . 5
Figure 2. Pin connection (top view) . . . 10
Figure 3. UVLO protection management . . . 12
Figure 4. Dual brush DC motor driver time diagram . . . 13
Figure 5. PARALLEL mode typical application . . . 14
Figure 6. PWM current control sequence example . . . 16
Figure 7. OFF time regulation circuit . . . 17
Figure 8. OFF time vs R_{OFF} value . . . 17
Figure 9. Overcurrent and short-circuit protections management . . . 18
Figure 10. Disable time versus R_{EN} and C_{EN} values (VDD = 3.3 V) . . . 19
Figure 11. Overcurrent threshold versus temperature (normalized at 25 °C) . . . 20
Figure 12. Thermal shutdown management . . . 21
Figure 13. ESD protection strategy . . . 22
Figure 14. Typical application schematic . . . 23
Figure 15. PCB layout example (top layer) . . . 24
Figure 16. TFQFPN 4 x 4 x 1.05 - 24 L package outline . . . 25
Figure 17. TFQFPN 4 x 4 x 1.05 - 24 L suggested footprint . . . 26

chanhvinh.com

1 Block diagram

Figure 1. Block diagram (general)



chanhvinh.com

2 Electrical data

2.1 Absolute maximum ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Test condition	Value	Unit
V_S	Supply voltage	-	-0.3 to 48	V
V_{IN}	Logic input voltage	-	-0.3 to 5.5	V
$V_{OUT,diff}$	Differential voltage between VSx, OUT1x, OUT2x and SENSEx pins	-	up to 48	V
V_{SENSE}	Sense pins voltage(1)	-	-2 to 2	V
V_{REFX}	Reference voltage input	-	-0.3 to 2	V
$I_{OUT,RMS}$	Continuous power stage output current (each full bridge)	-	1.5	A_{rms}
T_j	Junction temperature	-	-40 to 150	°C
T_{stg}	Storage temperature	-	-55 to 150	°C

1. SENSEA1, SENSEA2, SNSA, SENSEB1, SENSEB2, SNSB.

2.2 Recommended operating conditions

Table 2. Recommended operating conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
V_S	Supply voltage	7	-	45	V
V_{IN}	Logic input voltage		-	5	V
V_{SENSE}	Sense pins voltage	-1	-	+1	V
V_{REFX}	Reference voltage input	0.1	-	1	V

chanhvinh.com

2.3 Thermal data

Table 3. Thermal data

Symbol	Parameter	Conditions	Value	Unit
R_{thJA}	Junction to ambient thermal resistance	Natural convection, according to JESD51-2a(1)	36.5	°C/W
$R_{thJCtop}$	Junction to case thermal resistance (top side)	Cold plate on top package, according to JESD51-12(1)	27.6	°C/W
$R_{thJCbot}$	Junction to case thermal resistance (bottom side)	Cold plate on exposed pad, according to JESD51-12(1)	5.9	°C/W
R_{thJB}	Junction to board thermal resistance	According to JESD51-8(1)	13.6	°C/W
Ψ_{JT}	Junction to top characterization	According to JESD51-2a(1)	1	°C/W
Ψ_{JB}	Junction to board characterization	According to JESD51-2a(1)	13.7	°C/W

1. Simulated on a 76.2 x 114.3 x 1.6 mm, with vias underneath the component, 2s2p board as per standard JEDEC (JESD51-7) in natural convection.

2.4 ESD protection ratings

Table 4. ESD protection ratings

Symbol	Parameter	Conditions	Class	Value	Unit
HBM	Human body model	Conforming to ANSI/ESDA/JEDEC JS001	H2	2	kV
CDM	Charge device model	Conforming to ANSI/ESDA/JEDEC JS002 All pins	C2a	500	V
		Conforming to ANSI/ESDA/JEDEC JS002 Corner pins only (1, 6, 7, 12, 13, 18, 19, 24)	-	750	V
MM	Machine model	Conforming to EIA/JESD22-A115-C	NC	200	V

chanhvinh.com

3 Electrical characteristics

Testing conditions: V_S = 36 V, T_j = 25 °C unless otherwise specified.

Table 5. Electrical characteristics

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
General						
$V_{Sth(ON)}$	V_S turn-on threshold	V_S rising from 0 V	-	6.0	6.5	V
$V_{Sth(HYST)}$	V_S turn-off threshold hysteresis	V_S falling from 7 V	-	0.4	-	V
I_S	V_S supply current	No commutations ENx = '0' R_{TOFF} = 10 kΩ	-	2.3	2.7	mA
		No commutations ENx = '1' R_{TOFF} = 10 kΩ	-	2.7	3	mA
V_{STBYL}	Standby low voltage	-	-	-	0.8	V
V_{STBYH}	Standby high voltage	-	2	-	-	V
$I_{S, STBY}$	V_S supply standby current	STBY = '0'	-	-	45	µA
Power stage						
$R_{DSon\ HS+LS}$	Total on resistance HS + LS	V_S = 21 V I_{OUT} = 1 A	-	1	1.3	Ω
		V_S = 21 V I_{OUT} = 1 A Tj = 150 °C(1)	-	1.4	1.6	
I_{DSS}	Output leakage current	OUTx = V_S = 48 V	-	-	20	µA
		OUTx = -0.3 V	-1	-	-	
V_{DF}	Freewheeling diode forward voltage	I_D = 1.5 A	-	1	-	V
t_{rise}	Rise time	V_S = 21 V	-	120	-	ns
t_{fall}	Fall time	V_S = 21 V	-	60	-	ns
Logic IO						
V_{IH}	High logic level input voltage	-	2	-	-	V
V_{IL}	Low logic level input voltage	-	-	-	0.8	V
V_{OL}	Low logic level output voltage	I_{OL} = 4 mA	-	-	0.3	V
$V_{RELEASE}$	FAULT open drain release voltage	-	-	-	0.6	V
R_{STBY}	STBY pull-down resistance	-	-	60	-	kΩ
I_{ENx}	Enable pull-down current	-	-	5	-	µA
t_{ENxd}	Enable input propagation delay	From ENx falling edge to OUTx high impedance	-	400	-	ns
$t_{PWM,d(ON)}$	PWM turn-on propagation delay	(2)	-	450	-	ns

chanhvinh.com

Table 5. Electrical characteristics (continued)

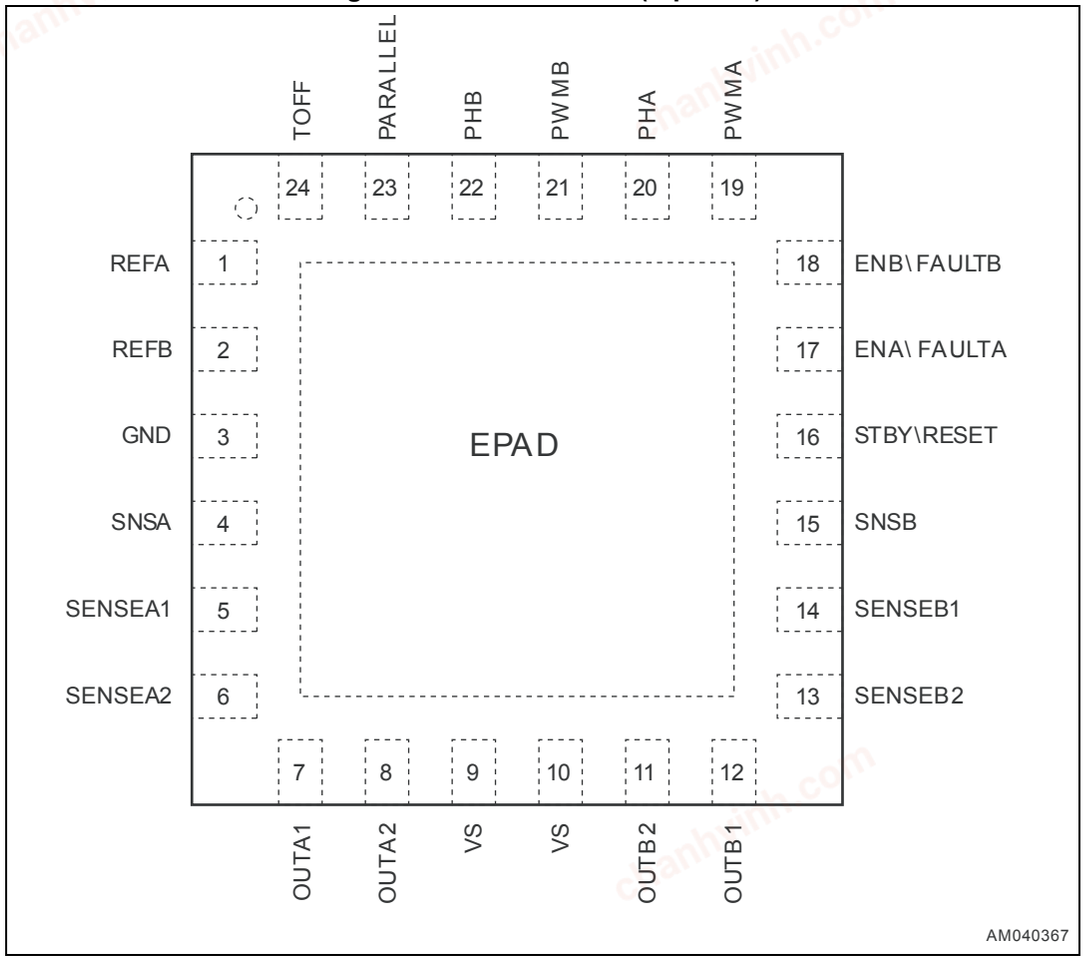
Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
$t_{PWM,d(OFF)}$	PWMx turn-off propagation delay	(2)	-	250	-	ns
$t_{PH,d}$	PHx propagation delay	(2)	-	450	-	ns
PWM current control						
$V_{SNS,OFFSET}$	Current control offset	-	-15	-	15	mV
t_{BLANK}	Blanking time	-	-	1.5	-	µs
t_{OFF}	Total OFF time	R_{OFF} = 10 kΩ	-	13	-	µs
		R_{OFF} = 160 kΩ	-	146	-	µs
Δ_{tOFF}	OFF time precision	Full temperature range(1)	-20	-	+20	%
$t_{OFF,jitter}$	Total OFF time jittering	-	-	±2	-	
Protections						
T_{jSD}	Thermal shutdown threshold	-	-	160	-	°C
$T_{jSD,Hyst}$	Thermal shutdown hysteresis	-	-	40	-	°C
I_{OC}	Overcurrent protection threshold	-	-	3	3.5	A

1. Based on characterization data on a limited number of samples, not tested during production.
2. See *Figure 4*.

chanhvinh.com

4 Pin connection

Figure 2. Pin connection (top view)



Note: The exposed pad must be connected to ground.

Table 6. Pin description

No.	Name	Type	Function
1	REFA	Analog input	Reference voltage for the PWM current control circuitry (side A)
2	REFB	Analog input	Reference voltage for the PWM current control circuitry (side B)
3, EPAD	GND	Ground	Device ground
4	SNSA	Analog input	Full bridge A current regulator sense input
5	SENSEA1	Power output	Sense output of the bridge A
6	SENSEA2	Power output	Sense output of the bridge A
7	OUTA1	Power output	Power bridge output side A1
8	OUTA2	Power output	Power bridge output side A2

chanhvinh.com

Table 6. Pin description (continued)

No.	Name	Type	Function
9	VS	Supply	Device supply voltage
10	VS	Supply	Device supply voltage
11	OUTB2	Power output	Power bridge output side B2
12	OUTB1	Power output	Power bridge output side B1
13	SENSEB2	Power output	Sense output of the bridge B
14	SENSEB1	Power output	Sense output of the bridge B
15	SNSB	Analog input	Full bridge B current regulator sense input
16	STBY\ RESET	Logic input	Standby\Reset input. When forced low the device enter in low consumption mode
17	ENA\ FAULTA	Logic input\ open drain output	Logic input 5 V compliant with open drain output. This is the full bridge A enable (when low, the power stage is turned off) and is forced low through the integrated open-drain MOSFET when a failure occurs.
18	ENB\ FAULTB	Logic input\ open drain output	Logic input 5 V compliant with open drain output. This is the full bridge B enable (when low, the power stage is turned off) and is forced low through the integrated open-drain MOSFET when a failure occurs.
19	PWMA	Logic input	Full bridge A PWM input
20	PHA	Logic input	Full bridge A current direction input
21	PWMB	Logic input	Full bridge B PWM input
22	PHB	Logic input	Full bridge B current direction input
23	PARALLEL	Logic input	Parallel mode input (see paragraph PARALLEL mode)
24	TOFF	Analog input	Internal oscillator frequency adjustment.

chanhvinh.com

5 Detailed description

The STSPIN840 is a dual brush DC motor driver integrating two PWM current controllers and a power stage composed of two fully-protected full-bridges.

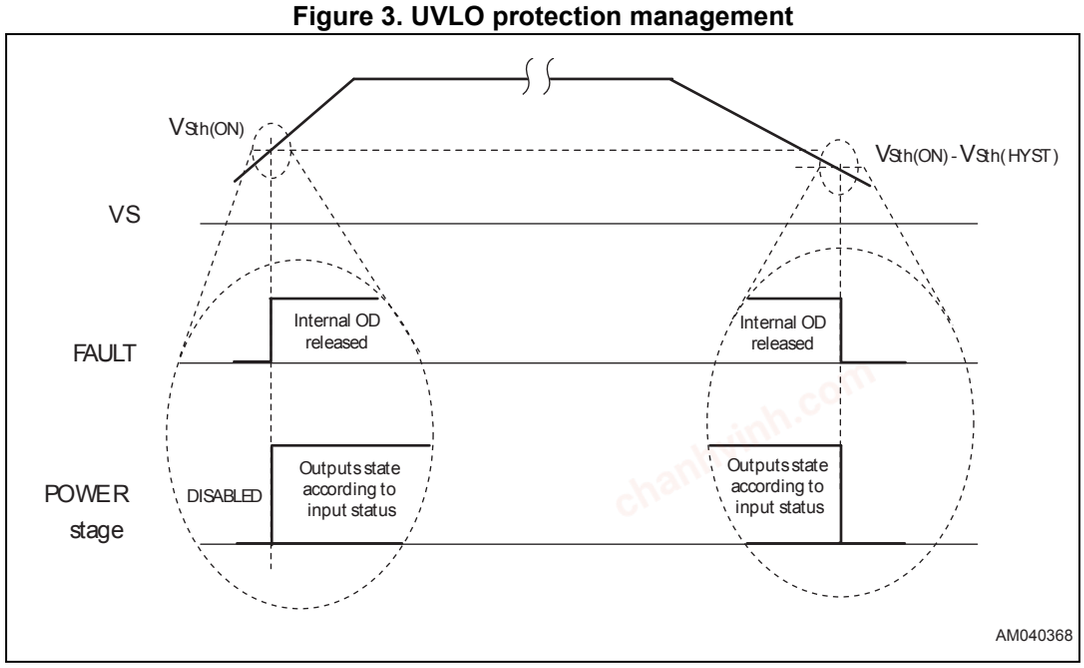
5.1 Power supply and standby

The device is supplied through the VS pins, the two pins must be at the same voltage.

At power-up the power stage is disabled and the FAULT pins are forced low until the V_S voltage rise above the $V_{Sth(ON)}$ threshold.

If the V_S falls below the $V_{Sth(ON)}$ - $V_{Sth(HYST)}$ value power stage is immediately disabled and the FAULT pins are forced low.

Figure 3. UVLO protection management



The device provides a low consumption mode, which is set by forcing the STBY\RESET input below the V_{STBYL} threshold.

When the device is in standby status the power stage is disabled (outputs are at high impedance) and the supply to the integrated control circuitry is strongly reduced. When the device leaves the standby status, all the control circuitry is reset to the power-up condition.

chanhvinh.com

5.2 Logic inputs

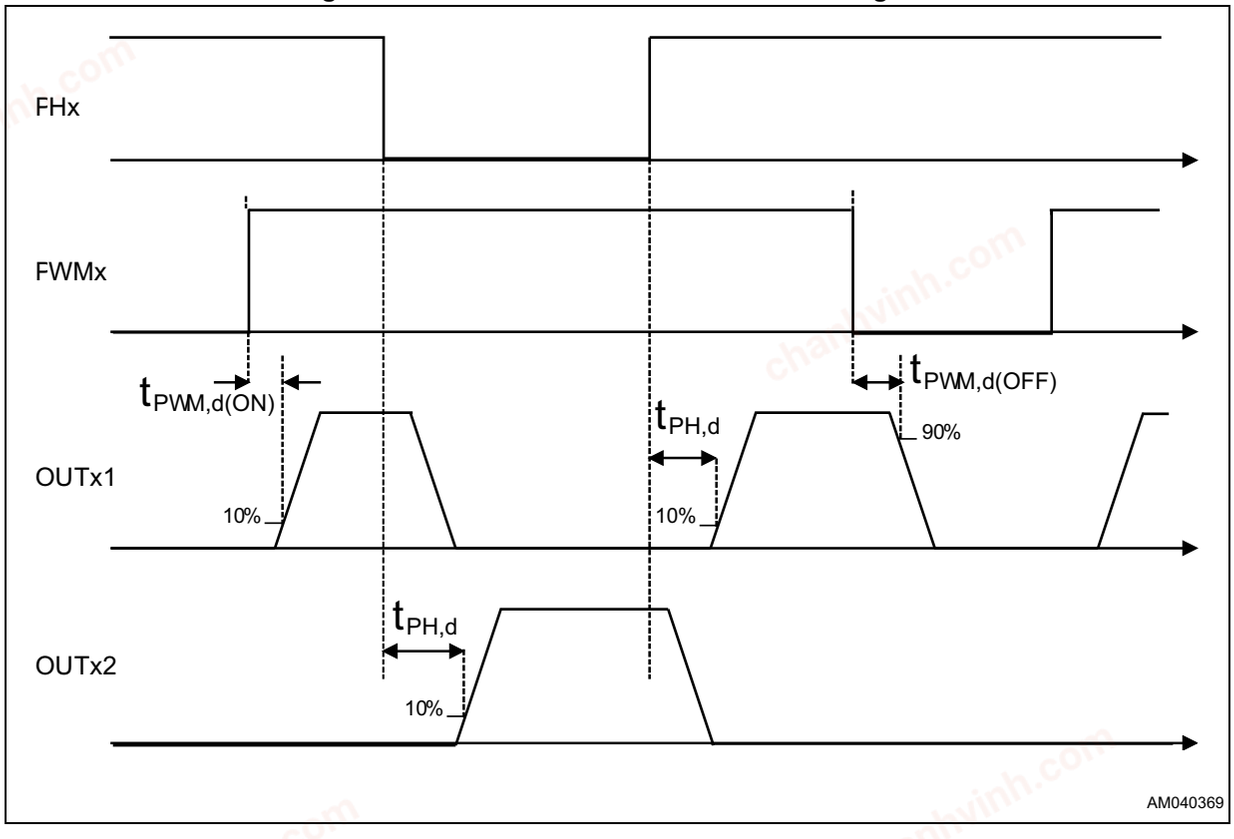
The outputs of each full bridge are controlled by the respective PWMx and PHx inputs. The status of the power bridge is also determined by the PWM current controller as indicated in *Section 5.3*.

Table 7. Truth table

ENx	PHx	PWMx	OUTx1	OUTx2	Full bridge condition
0	X(1)	X(1)	High Z(2)	High Z(2)	Disabled
1	0	0	GND	GND	Both LS on
1	0	1	GND	VS	HS2 and LS1 on (current OUTx1 → OUTx2)
1	1	0	GND	GND	Both LS on
1	1	1	VS	GND	HS1 and LS2 on (current OUTx1 → OUTx2)

1. X: don't care.
2. High Z: high impedance.

Figure 4. Dual brush DC motor driver time diagram



chanhvinh.com

PARALLEL mode

The device can operate in parallel mode by forcing the PARALLEL input pin high.

In this operation mode both the full bridges are driven by the ENA, PWMA and PHA inputs. The PWM current control comparator of the bridge B is disabled, and bridge A one drives both the power stages.

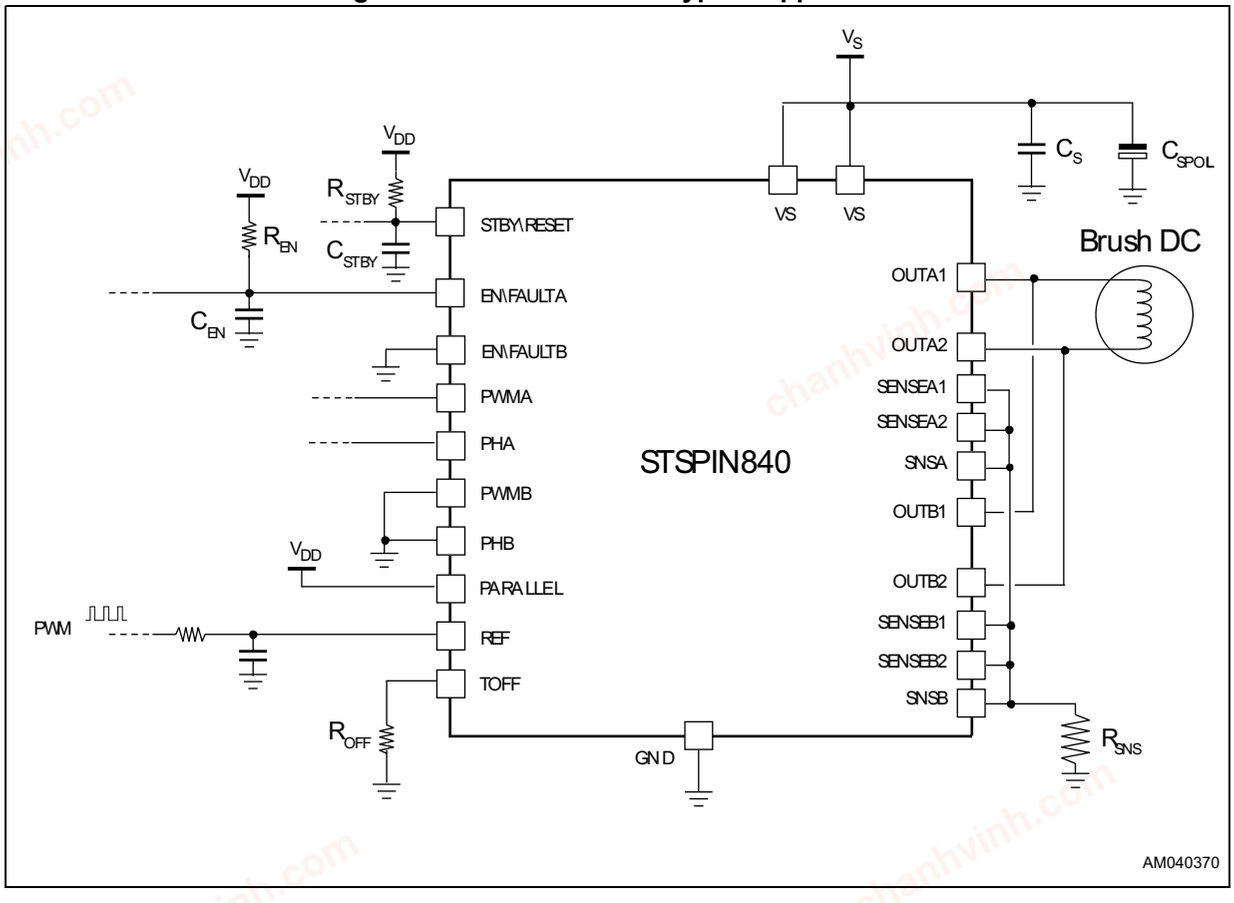
The resulting single full-bridge power stage allows an increase in the output current capability and reduce the device power dissipation. The outputs and sense pins configuration must be:

- OUT1A connected with OUT1B
- OUT2A connected with OUT2B
- All SENSE and SNS pins connected together as shown in *Figure 5*.

The ENA\FAULTA pin is also used as FAULT indication through the integrated open-drain MOSFETs as described in *Section 5.4* and *Section 5.4.3 on page 21*.

Note: In parallel mode the ENB\FAULTB pin is forced low.

Figure 5. PARALLEL mode typical application



chanhvinh.com

5.3 PWM current control

The device implements two independent PWM current controllers, one for each full bridge.

The bridge current is sensed through the SNS pins monitoring the voltage drop across an external resistor connected between the source of the low side power MOSFET (SENSE pins) and ground.

The voltage of the SNS pins (V_{SNSA} and V_{SNSB}) is compared to the respective reference voltage pin (V_{REFA} and V_{REFB}).

When $V_{SNSX} > V_{REFX}$ the current limiter is triggered, the OFF time counter is started and the low sides of the full bridge are turned on (slow decay) until the end of count of the timer.

During current decays the inputs values are ignored until the system returns to ON condition (decay time expired).

Table 8. ON and slow decay states

PHx(1)	PWMx(1)	ON	Slow decay
0	0	HSx1 = OFF **LSx1 = ON** HSx2 = OFF **LSx2 = ON**	HSx1 = OFF **LSx1 = ON** HSx2 = OFF **LSx2 = ON**
0	1	HSx1 = OFF **LSx1 = ON** **HSx2 = ON** LSx2 = OFF	HSx1 = OFF **LSx1 = ON** HSx2 = OFF **LSx2 = ON**
1	0	HSx1 = OFF **LSx1 = ON** HSx2 = OFF **LSx2 = ON**	HSx1 = OFF **LSx1 = ON** HSx2 = OFF **LSx2 = ON**
1	1	**HSx1 = ON** LSx1 = OFF HSx2 = OFF **LSx2 = ON**	HSx1 = OFF **LSx1 = ON** HSx2 = OFF **LSx2 = ON**

1. When the device works in parallel mode the PHA and PWMA inputs drive both Full bridge A and B.

The reference voltage value, V_{REF}, has to be selected according the load current target value (peak value) and sense resistors value.

Equation 1

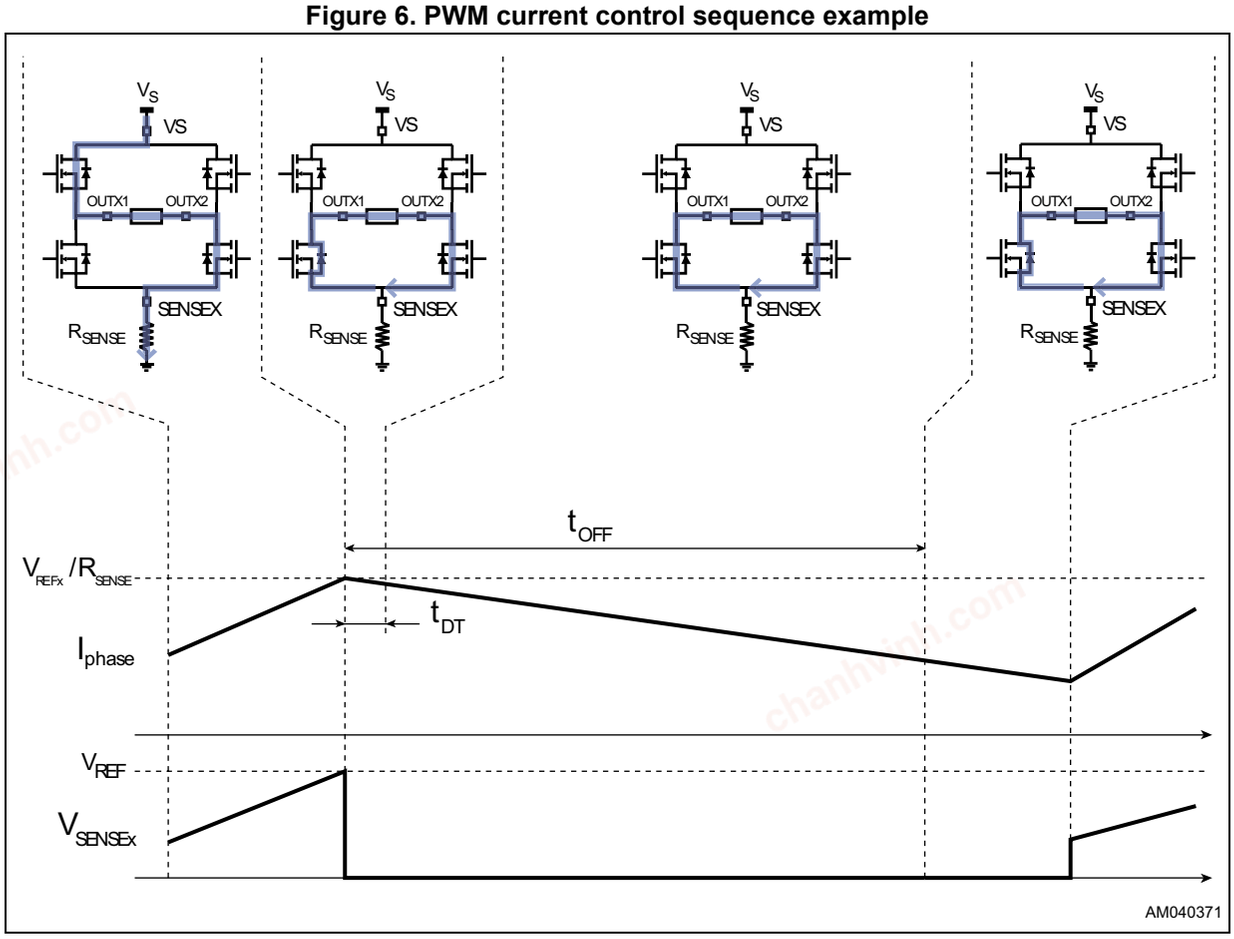
$$V_{REF} = R_{SENSE} \times I_{LOAD,peak}$$

chanhvinh.com

The choice of sense resistors value must be take into account two main issues:

- The sensing resistor dissipates energy and provides dangerous negative voltages on the SENSE pins during the current recirculation. For this reason the resistance of this component should be kept low (using multiple resistors in parallel will help obtaining the required power rating with standard resistors).
- The lower is the RSENSE value, the higher is the peak current error due to noise on V_{REF} pin and to the input offset of the current sense comparator: too small values of RSENSE must be avoided.

Figure 6. PWM current control sequence example



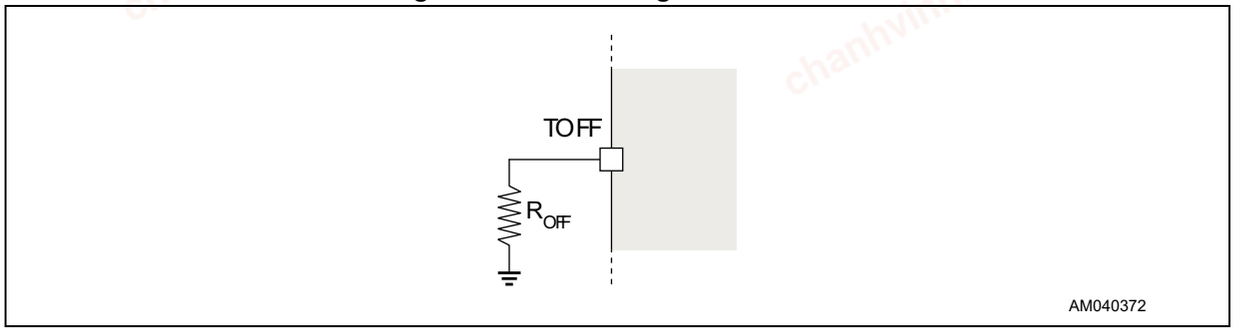
Note: When the voltage on the SNSx pin exceeds the absolute ratings, a fault condition is triggered and the respective ENx\FAULTx output is forced low.

chanhvinh.com

TOFF adjustment

The OFF time is adjusted through an external resistor connected between the TOFF pin and ground as shown in *Figure 7*.

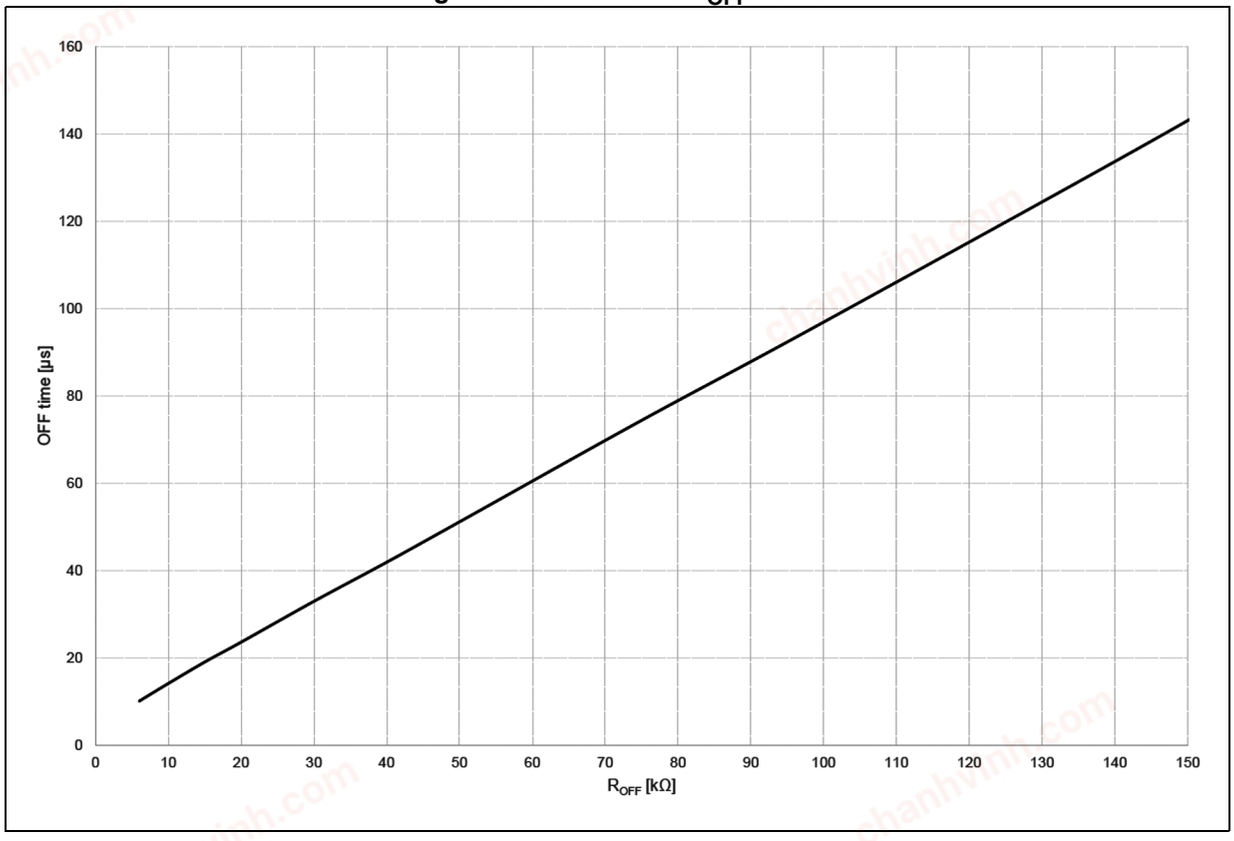
Figure 7. OFF time regulation circuit



The relation between the OFF time and the external resistor value is shown in the graph of *Figure 8*. The value typically ranges from 10 µs to 150 µs.

The recommended value for R_{OFF} is in the range between 5 kΩ and 180 kΩ.

Figure 8. OFF time vs R_{OFF} value



chanhvinh.com

5.4 Device protections

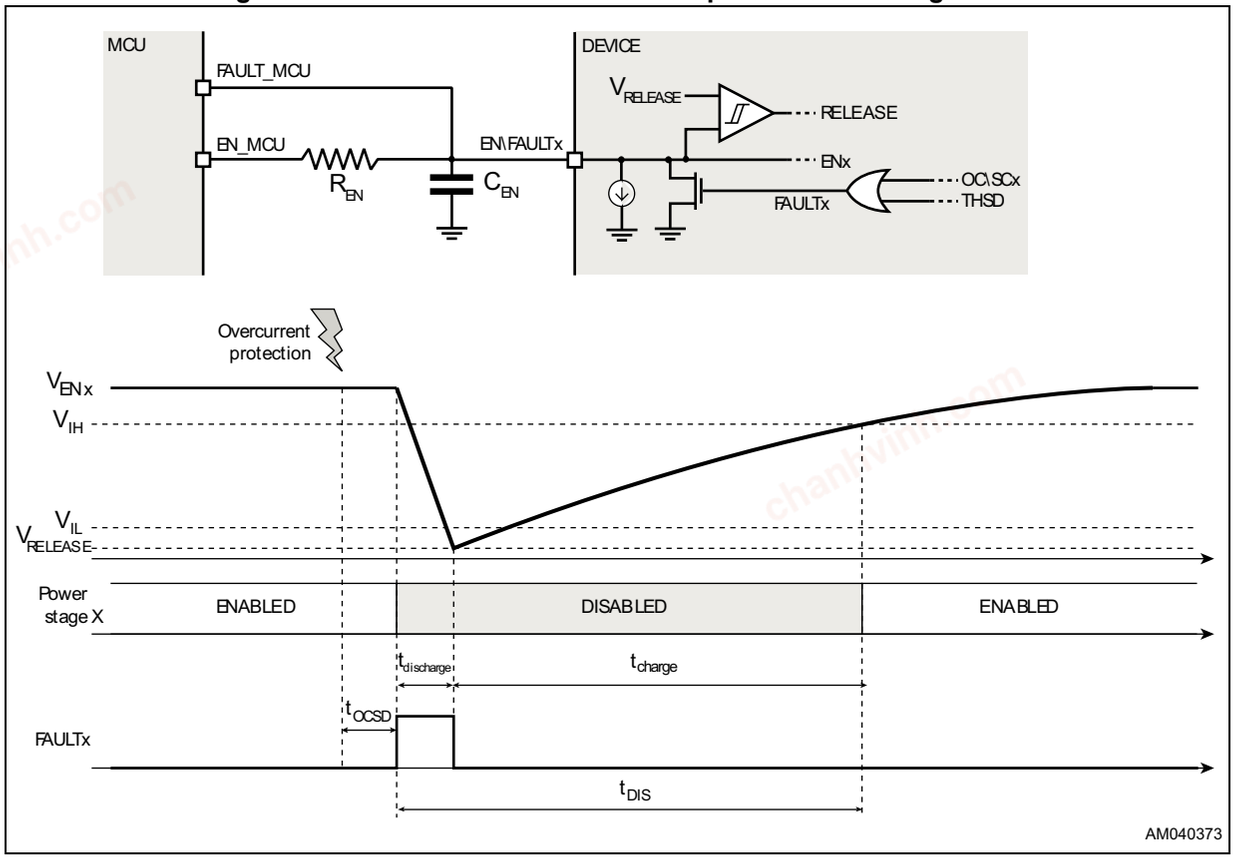
5.4.1 Overcurrent and short-circuit protections

The device has circuitry embedded to protect each power MOSFET against the overload and short-circuit conditions (short-circuit to ground, short-circuit to VS and short-circuit between outputs).

When the overcurrent or the short-circuit protection is triggered the respective power stage is disabled and the relative EN\FAULT input is forced low through the integrated open-drain MOSFET discharging the external C_{EN} capacitor (refer to *Figure 9*).

The power stage is kept disabled and the open-drain MOSFET is kept ON until the EN\FAULT input falls below the $V_{RELEASE}$ threshold, then the C_{EN} capacitor is charged through the external R_{EN} resistor.

Figure 9. Overcurrent and short-circuit protections management



The total disable time after an overcurrent event is set sizing properly the external network connected to EN\FAULT pins (refer to *Figure 10*) and it is the sum of the discharging and charging time of the C_{EN} capacitor:

Equation 2

$$t_{DIS} = t_{discharge} + t_{charge}$$

chanhvinh.com

Considering $t_{discharge}$ is normally significantly lower than t_{charge}, its contribution is negligible and the disable time is almost equal to t_{charge} only:

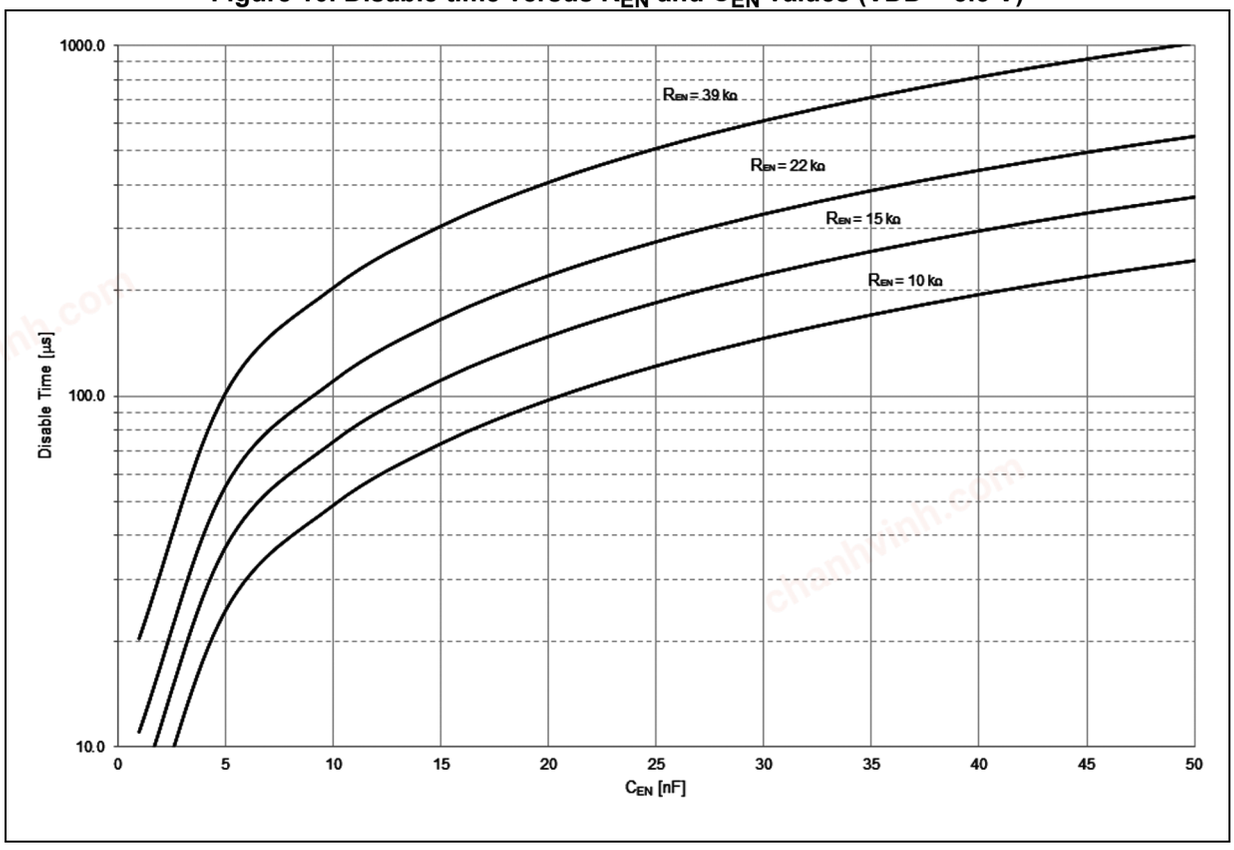
Equation 3

$$t_{DIS} \cong R_{EN} \times C_{EN} \times I_n \frac{(V_{DD} - R_{EN} \times I_{PD}) - V_{RELEASE}}{(V_{DD} - R_{EN} \times I_{PD}) - V_{IH}}$$

Where V_{DD} is the pull-up voltage of R_{EN} resistor.

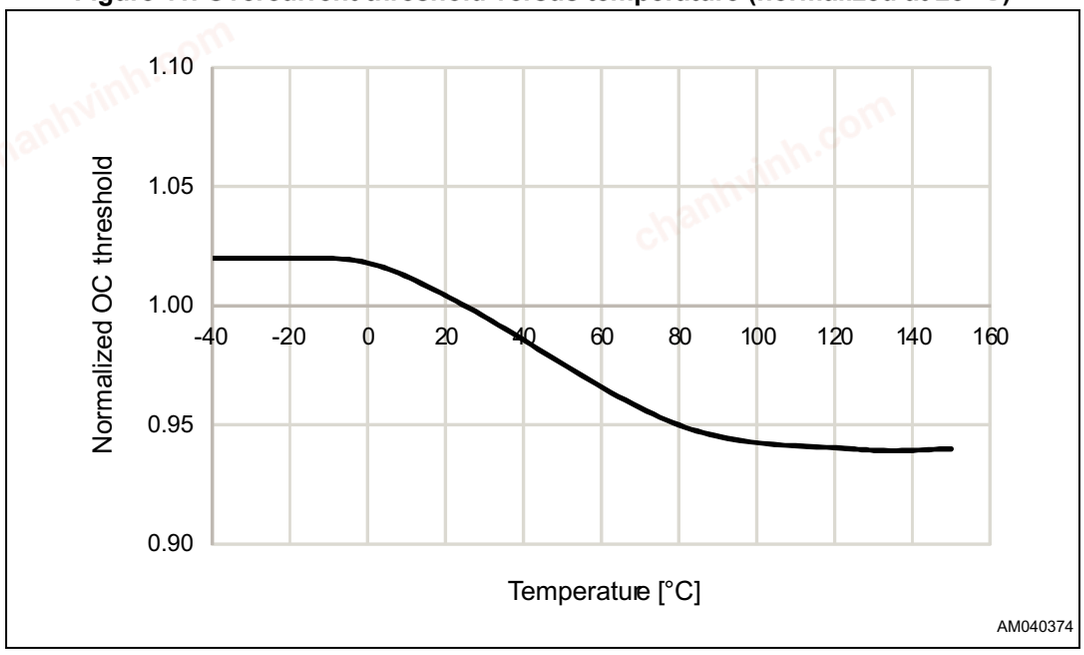
The recommended value for R_{EN} and C_{EN} are respectively 39 kΩ and 10 nF that allow obtaining 300 µs disable time.

Figure 10. Disable time versus R_{EN} and C_{EN} values (VDD = 3.3 V)



chanhvinh.com

Figure 11. Overcurrent threshold versus temperature (normalized at 25 °C)



5.4.2 Thermal shutdown

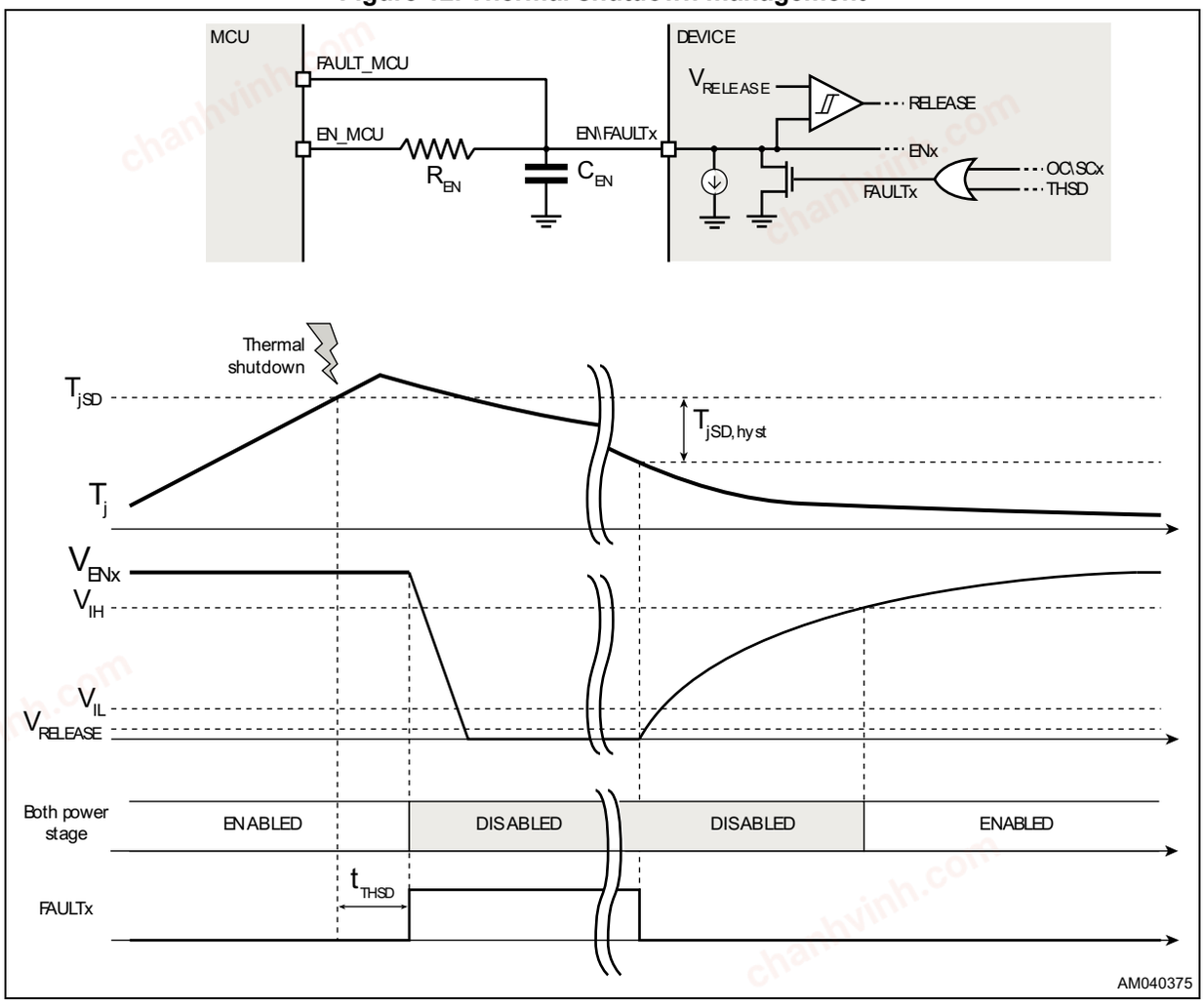
The device has circuitry embedded to protect it from overtemperature conditions.

When the thermal shutdown temperature is reached both the power bridge are disabled and both the EN\FAULT inputs are forced low through the integrated open-drain MOSFETs (refer to *Figure 12*).

The protection and the EN\FAULT outputs are released when the IC temperature returns below a safe operating value (T_{jSD} - $T_{jSD,Hyst}$).

chanhvinh.com

Figure 12. Thermal shutdown management



5.4.3 Blanking time

The device provides a blanking time t_{BLANK} after each power MOSFET commutation to prevent false triggering of protections and current control.

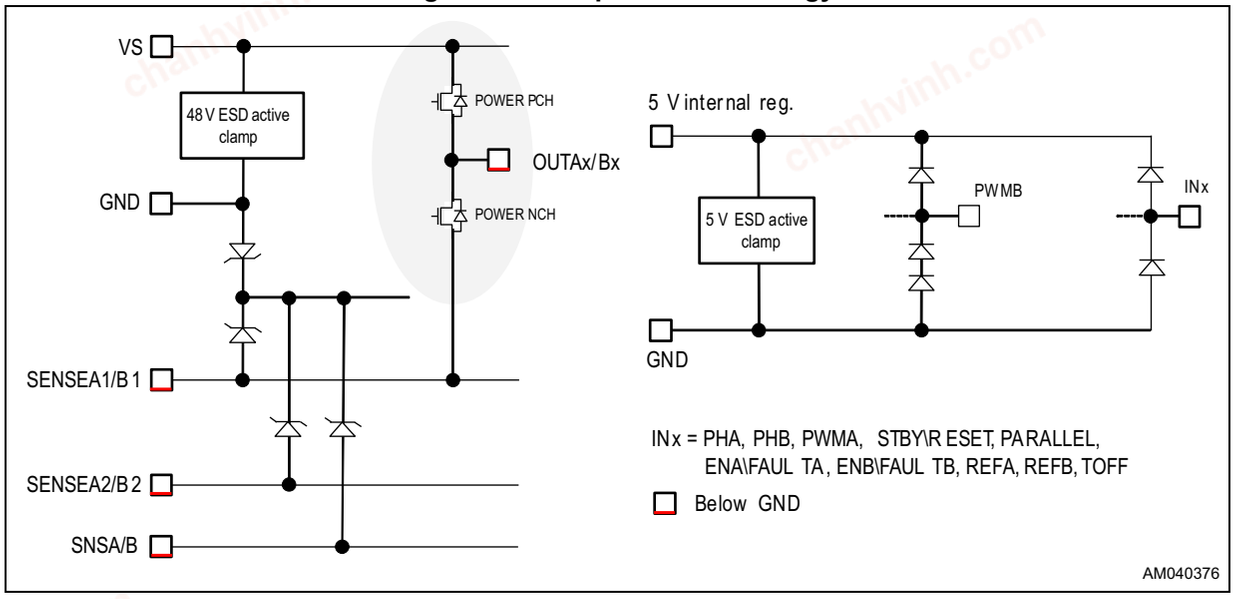
During blanking time the following circuits are inhibited:

- Overcurrent and short-circuit protections of commutating power stage
- Current control comparator of the commutating power stage
- Thermal protection of the commutating power stage.

chanhvinh.com

5.5 ESD protection strategy

Figure 13. ESD protection strategy



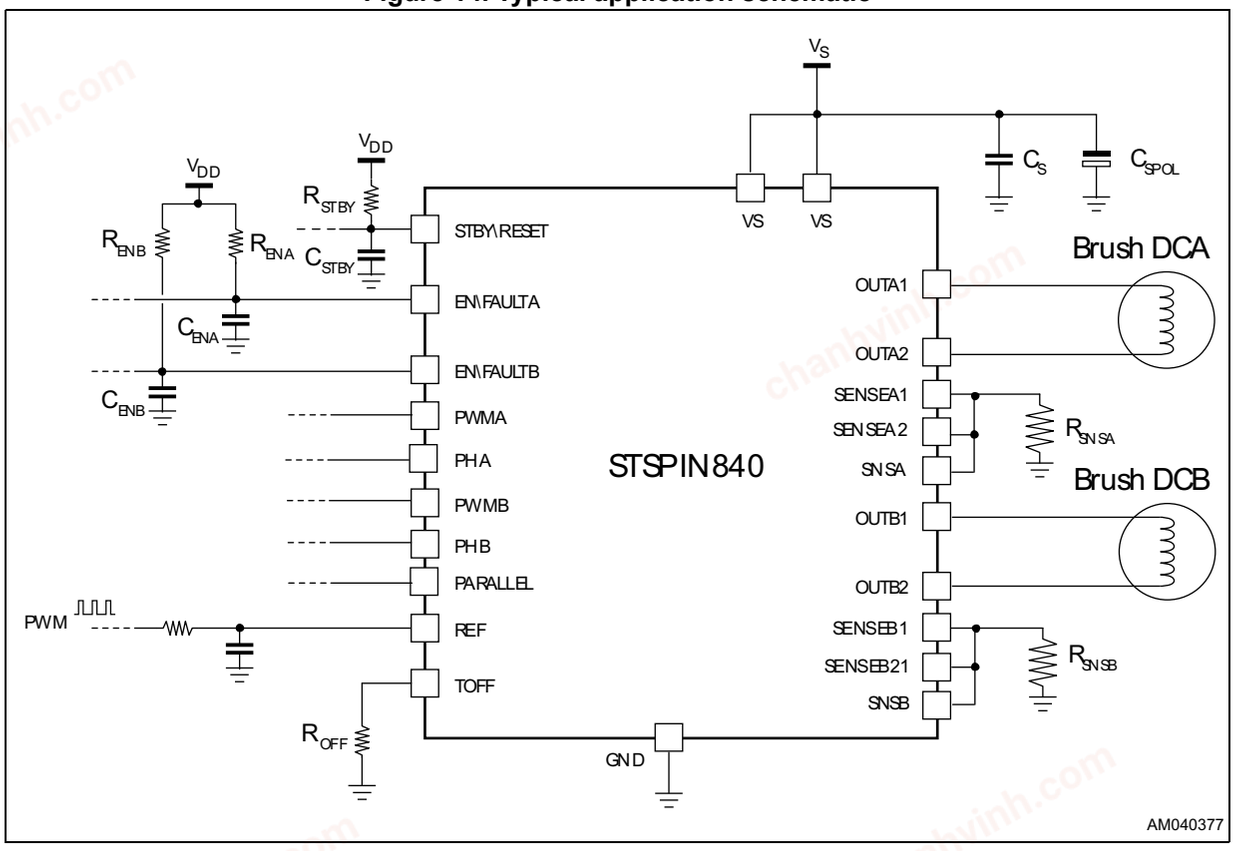
chanhvinh.com

6 Typical applications

Table 9. Typical application values

Name	Value
C_S	330 nF
C_{SPOL}	33 µF
R_{SNSA}, R_{SNSB}	330 mΩ / 1 W
C_{ENA}, C_{ENB}	10 nF
R_{ENA}, R_{ENB}	39 kΩ
C_{STBY}	1 nF
R_{STBY}	18 kΩ
R_{OFF}	10 kΩ ($T_{OFF} \cong$ 13 µs)

Figure 14. Typical application schematic



chanhvinh.com

7 Layout recommendations

The STSPIN840 device integrates the power stage; in order to improve the thermal dissipation, the exposed pad must be connected to the ground plane on the bottom layer using multiple vias equally spaced. This ground plane acts as a heatsink, for this reason it should be as wide as possible.

The voltage supply V_S must be stabilized and filtered with a ceramic bypass capacitor, typically 330 nF. It must be placed on the same side and as close as possible to the V_S pin in order to reject high frequency noise components on the supply. A bulk capacitor could also be required (typically a 33 µF). The connection between the power supply connector and the V_S pins must be as short as possible using wide traces.

In order to ensure the best ground connection between the STSPIN840 and the other components, a GND plane surrounding the device is recommended.

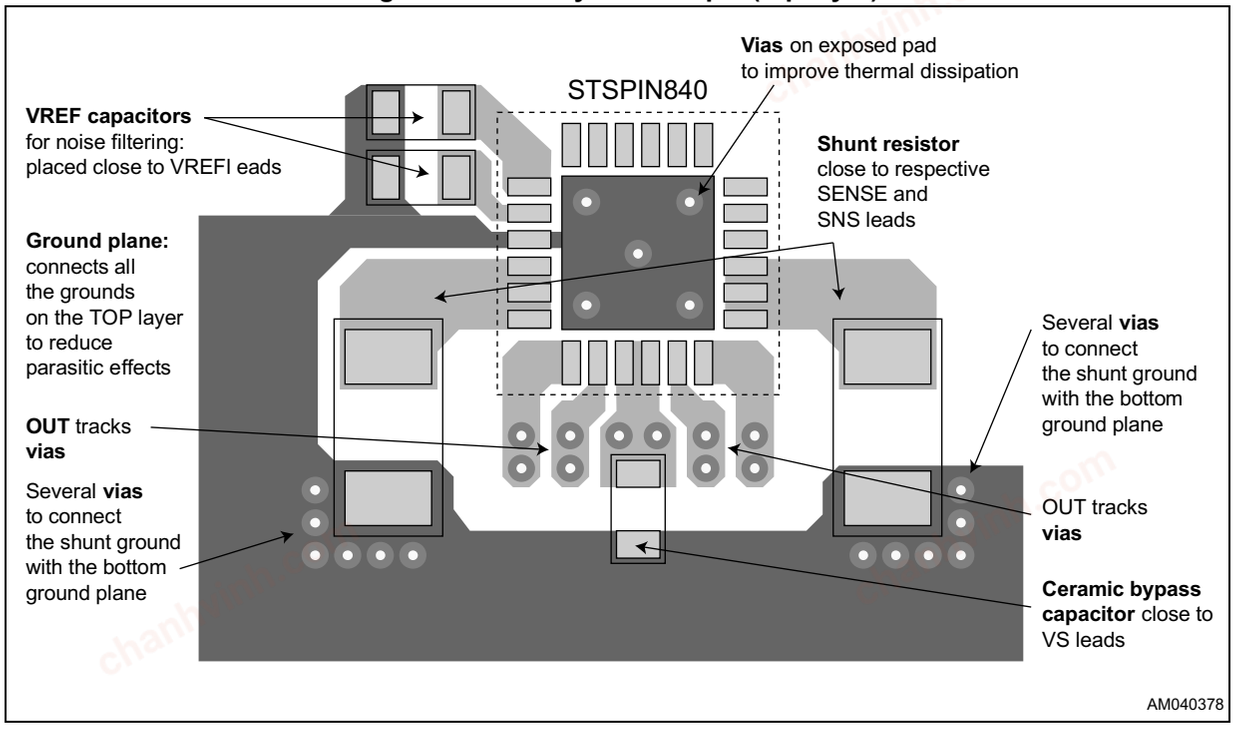
A capacitor between REF pins and ground should be positioned as near as possible to the device in order to filter the noise and stabilize the reference voltage.

Several vias should be positioned as near as possible each sense resistor connecting them to the ground plane on the bottom layer. In this way, both the GND planes provide a path for the current flowing into the power stage.

The path between the ground of the shunt resistors and the ceramic bypass capacitor of the device is critical; for this reason it must be as short as possible minimizing parasitic inductances that can cause voltage spikes on SENSE and OUT pins.

The OUT pins and the VS nets can be routed using the bottom layer, it is recommended to use two vias for output connections.

Figure 15. PCB layout example (top layer)



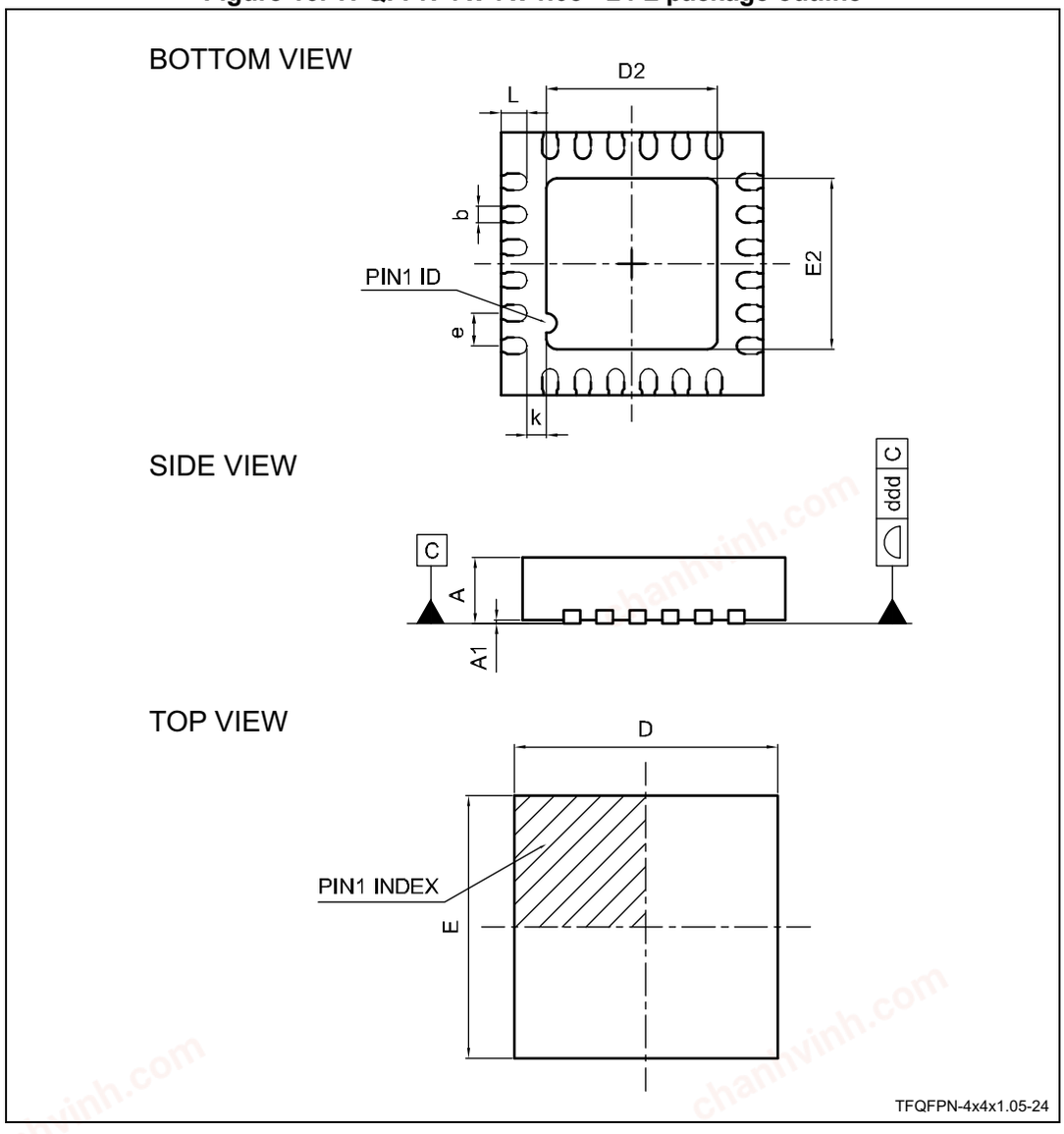
chanhvinh.com

8 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

8.1 TFQFPN TFQFPN 4 x 4 x 1.05 - 24 L package information

Figure 16. TFQFPN 4 x 4 x 1.05 - 24 L package outline



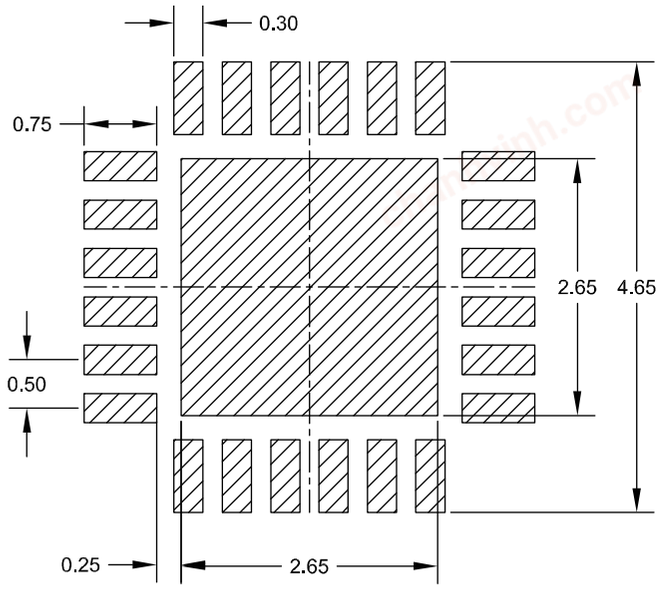
chanhvinh.com

Table 10. TFQFPN 4 x 4 x 1.05 - 24 L package mechanical data

Symbol	Dimensions (mm)			Note
	Min.	Typ.	Max.	
A	0.90	1.00	1.10	-
A1	0.00	0.02	0.05	-
b	0.20	0.25	0.30	(1)
D	3.90	4.00	4.10	-
D2	2.55	2.60	2.65	-
E	3.90	4.00	4.10	-
E2	2.55	2.60	2.65	-
e	-	0.50	-	-
L	0.35	0.40	0.45	
k	-	0.30	-	-
ddd	-	0.05	-	-

1. Dimension “b” does not include dambar protrusion. Allowable dambar protrusion shall not cause the lead width to exceed the maximum “b” dimension by more than 0.08 mm.

Figure 17. TFQFPN 4 x 4 x 1.05 - 24 L suggested footprint



TFQFPN 4 x 4 x 1.05 - 24 L

chanhvinh.com

9 Ordering information

Table 11. Device summary

Order code	Package	Packaging
STSPIN840	TFQFPN 4 x 4 x 1.05 - 24 L	Tape and reel

10 Revision history

Table 12. Document revision history

Date	Revision	Changes
18-May-2018	1	Initial release.

chanhvinh.com

chanhvinh.com

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2018 STMicroelectronics – All rights reserved